

IN THE SPECIFICATIONS:

Please replace paragraph [0039] with the following amended paragraph:

[0039] FIG. 2 shows a schematic sectional view illustrating a thin film deposition apparatus having a distributor according to a present invention. As shown in FIG. 2, the thin film deposition apparatus comprises a reaction chamber 110, a substrate heating member 120, a gas injector 130 and a substrate inlet/outlet [[140]] 150. Also, the reaction chamber 110 can be divided into three parts--a sidewall portion 111, a bottom portion 112 and a top portion 113. These sidewall 111, bottom 112 and top 113 portions define a reaction space inside the reaction chamber 110. In the meanwhile, the bottom portion 112 of the reaction chamber 110 includes a gas exhaust port that emits the air in the reaction chamber 110. The substrata substrate heating member 120 is disposed in the central reaction space of the reaction chamber 10 and supported by a ram 121 that is mounted through the bottom portion 112 of the reaction chamber 110. A substrate or silicon wafer (not shown), where the thin film is deposited, is placed upon the substrate heating member 120 during the deposition processes, and the substrate heating member 120 including a heater applies heat to the substrate or silicon wafer thereon. The substrate inlet/outlet 150 is positioned in the sidewall portion 111 of the reaction chamber 10, thereby taking the substrate or silicon wafer in or out of the reaction chamber 10 through this substrate inlet/outlet 150. Although FIG. 2 shows only one substrate inlet/outlet 150, another substrate inlet/outlet can be formed in the sidewall portion 111 opposite to the fit one, thereby acting as an entrance or exit for the substrate respectively.

Please replace paragraph [0055] with the following amended paragraph:

[0055] Accordingly within the principles of the present invention, since the distributor injects the source elements through the injection holes therein, the thin film has the uniform thickness upon the substrate. Also, since the Atomic Layer Deposition (AMD) (ALD) method is adopted in the present invention, the thin film deposited on the substrate has the uniform composition without the impurities.